MBR30H100CT

SWITCHMODE™ Power Rectifier 100 V, 30 A

Features and Benefits

- Low Forward Voltage: 0.67 V @ 125°C
- Low Power Loss/High Efficiency
- High Surge Capacity
- 175°C Operating Junction Temperature
- 30 A Total (15 A Per Diode Leg)
- Pb−Free Package is Available

Applications

- Power Supply − Output Rectification
- Power Management
- Instrumentation

Mechanical Characteristics:

- Case: Epoxy, Molded
- Epoxy Meets UL 94 V−0 @ 0.125 in
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- ESD Rating: Human Body Model = 3B; Machine Model = C

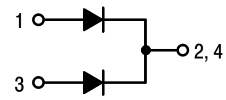
MAXIMUM RATINGS

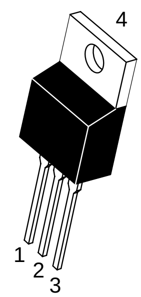
Please See the Table on the Following Page

ON Semiconductor®

http://onsemi.com

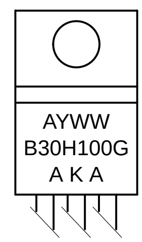
SCHOTTKY BARRIER RECTIFIER
30 AMPERES
100 VOLTS





TO−220AB
CASE 221A
PLASTIC

MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
B30H100 = Device Code
G = Pb−Free Package
AKA = Polarity Designator

ORDERING INFORMATION

Device	Package	Shipping
MBR30H100CT	TO−220	50 Units/Rail
MBR30H100CTG	TO−220 (Pb−Free)	50 Units/Rail

MAXIMUM RATINGS (Per Diode Leg)

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	100	V
Average Rectified Forward Current (T_C = 156°C) Per Diode Per Device	$I_{F(AV)}$	 15 30	A
Peak Repetitive Forward Current (Square Wave, 20 kHz, T_C = 151°C)	I_{FM}	30	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	250	A
Operating Junction Temperature (Note 1)	T_J	+175	°C
Storage Temperature	T_{stg}	– 65 to +175	°C
Voltage Rate of Change (Rated V_R)	dv/dt	10,000	V/μs
Controlled Avalanche Energy (see test conditions in Figures 11 and 12)	W_{AVAL}	200	mJ
ESD Ratings: Machine Model = C Human Body Model = 3B		> 400 > 8000	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. The heat generated must be less than the thermal conductivity from Junction−to−Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance − Junction−to−Case (Min. Pad) − Junction−to−Ambient (Min. Pad)	$R_{\theta JC}$ $R_{\theta JA}$	2.0 60	°C/W

ELECTRICAL CHARACTERISTICS (Per Diode Leg)

Characteristic	Symbol	Min	Typ	Max	Unit
Maximum Instantaneous Forward Voltage (Note 2) (i_F = 15 A, T_J = 25°C) (i_F = 15 A, T_J = 125°C) (i_F = 30 A, T_J = 25°C) (i_F = 30 A, T_J = 125°C)	v_F	 – – – –	 0.76 0.64 0.88 0.76	 0.80 0.67 0.93 0.80	V
Maximum Instantaneous Reverse Current (Note 2) (Rated DC Voltage, T_J = 125°C) (Rated DC Voltage, T_J = 25°C)	i_R	 – –	 1.1 0.0008	 6.0 0.0045	mA

2. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

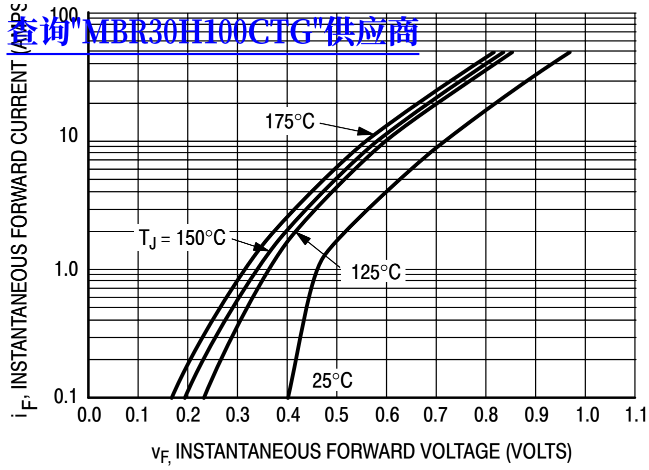


Figure 1. Typical Forward Voltage

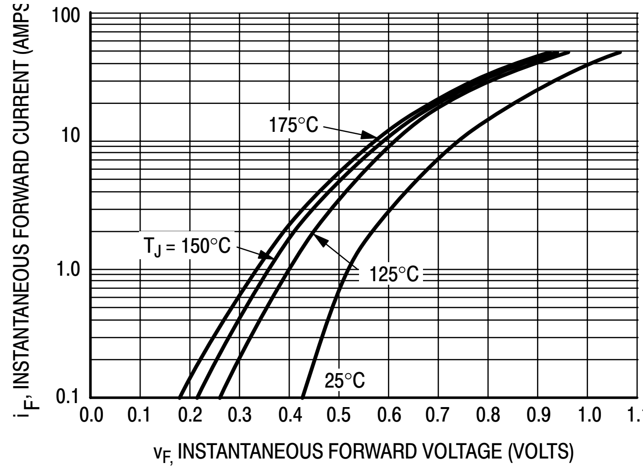


Figure 2. Maximum Forward Voltage

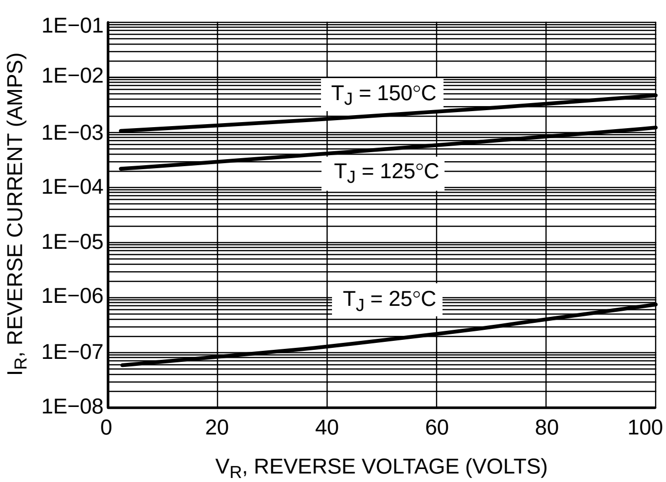


Figure 3. Typical Reverse Current

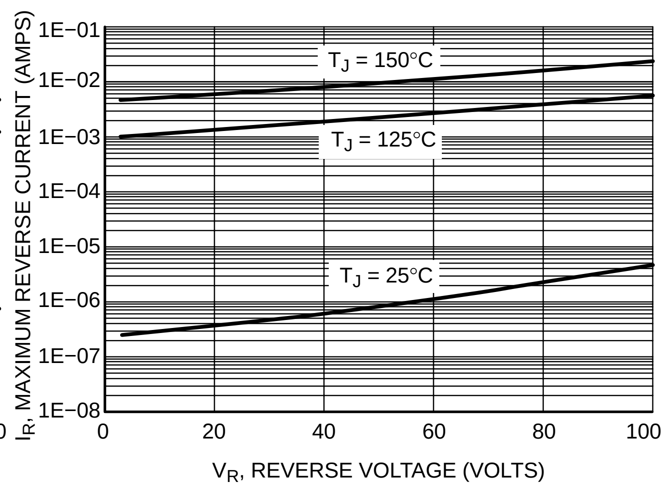


Figure 4. Maximum Reverse Current

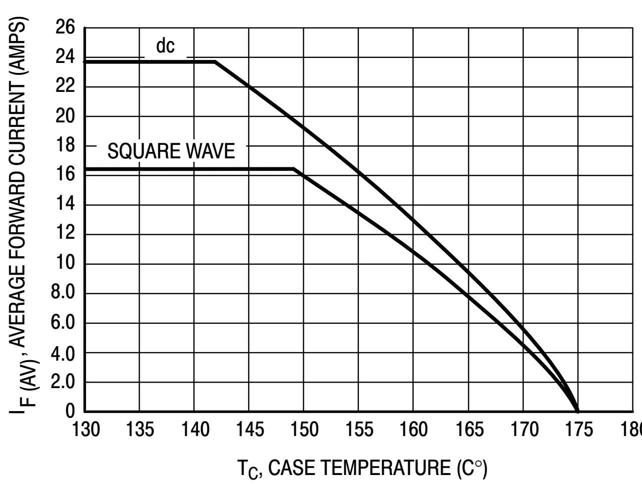


Figure 5. Current Derating, Case Per Leg

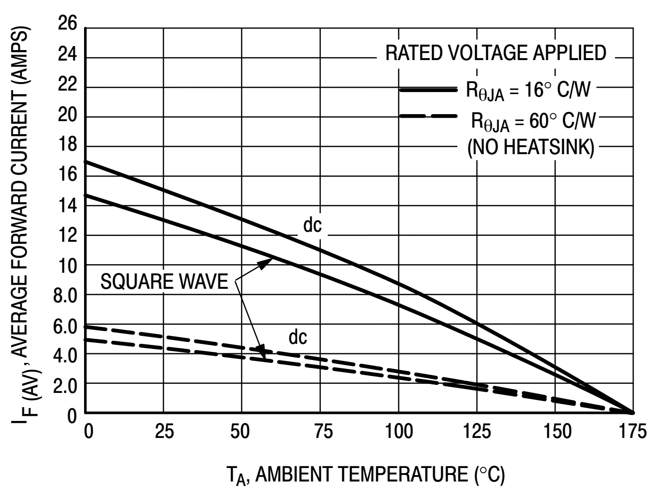


Figure 6. Current Derating, Ambient Per Leg

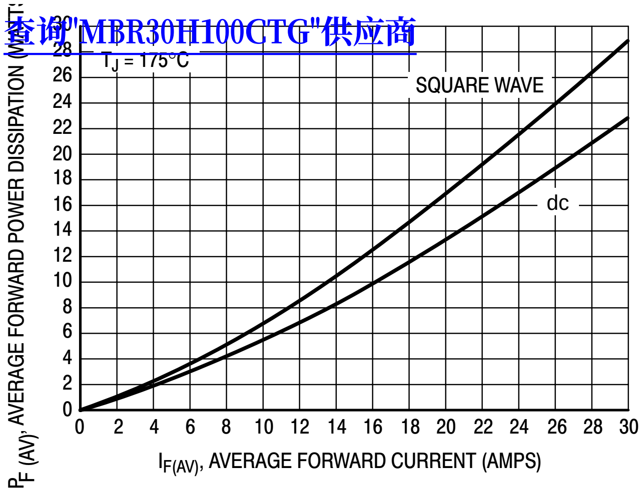


Figure 7. Forward Power Dissipation

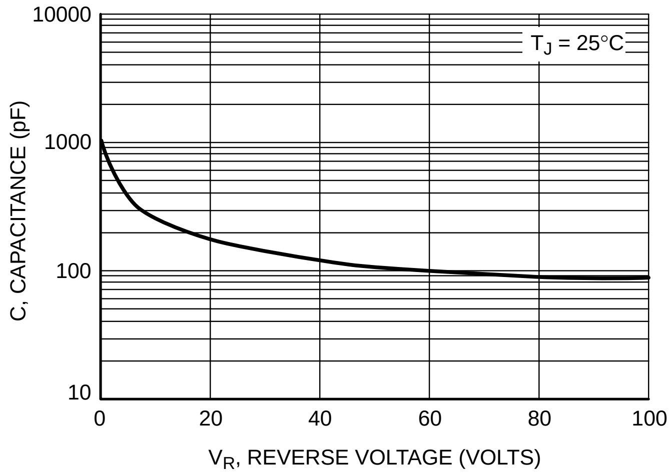


Figure 8. Capacitance

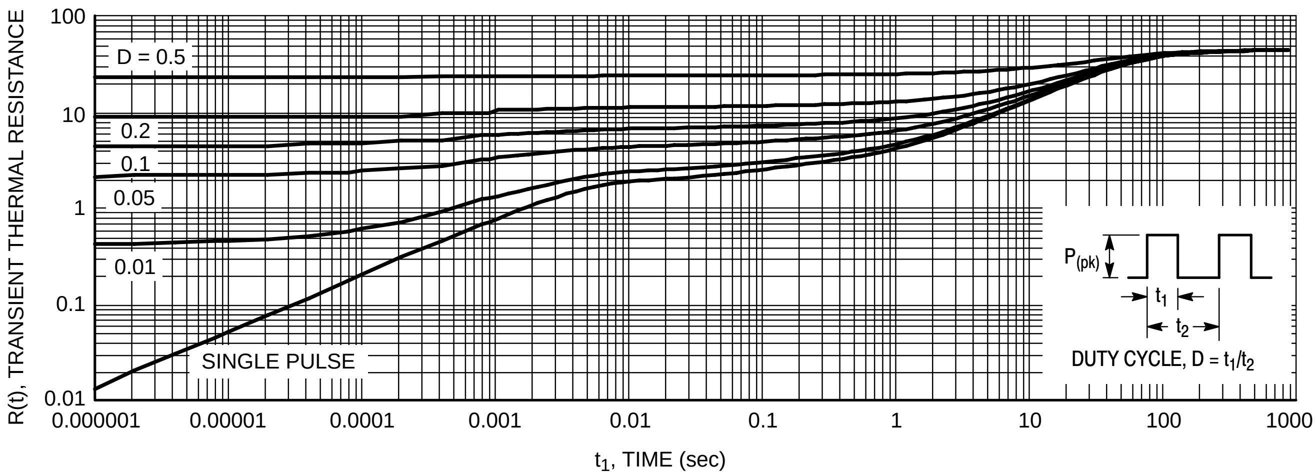


Figure 9. Thermal Response Junction−to−Ambient

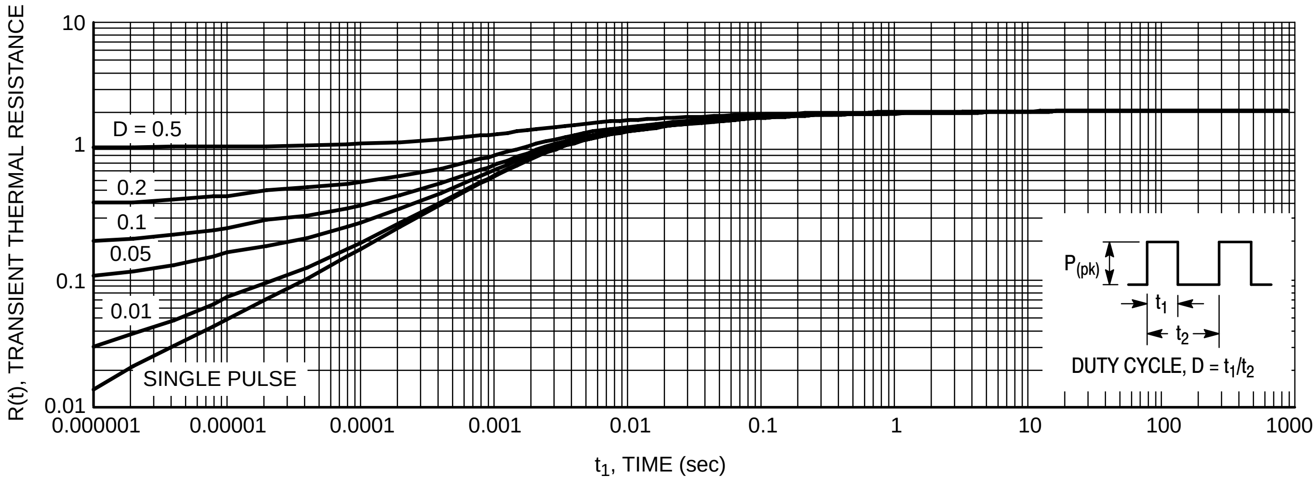


Figure 10. Thermal Response Junction−to−Case

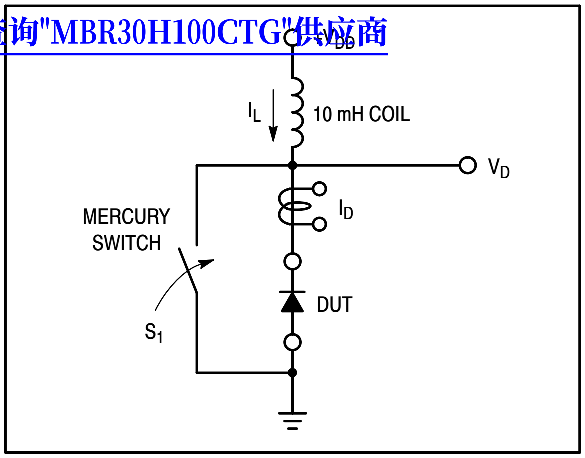


Figure 11. Test Circuit

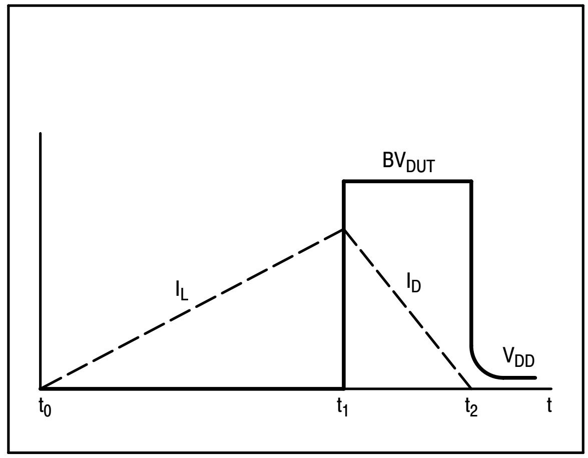


Figure 12. Current−Voltage Waveforms

The unclamped inductive switching circuit shown in Figure 11 was used to demonstrate the controlled avalanche capability of this device. A mercury switch was used instead of an electronic switch to simulate a noisy environment when the switch was being opened.

When S_1 is closed at t_0 the current in the inductor I_L ramps up linearly; and energy is stored in the coil. At t_1 the switch is opened and the voltage across the diode under test begins to rise rapidly, due to di/dt effects, when this induced voltage reaches the breakdown voltage of the diode, it is clamped at BV_{DUT} and the diode begins to conduct the full load current which now starts to decay linearly through the diode, and goes to zero at t_2.

By solving the loop equation at the point in time when S_1 is opened; and calculating the energy that is transferred to the diode it can be shown that the total energy transferred is equal to the energy stored in the inductor plus a finite amount of energy from the V_{DD} power supply while the diode is in breakdown (from t_1 to t_2) minus any losses due to finite component resistances. Assuming the component resistive elements are small Equation (1) approximates the total energy transferred to the diode. It can be seen from this equation that if the V_{DD} voltage is low compared to the breakdown voltage of the device, the amount of energy contributed by the supply during breakdown is small and the total energy can be assumed to be nearly equal to the energy stored in the coil during the time when S_1 was closed, Equation (2).

EQUATION (1):

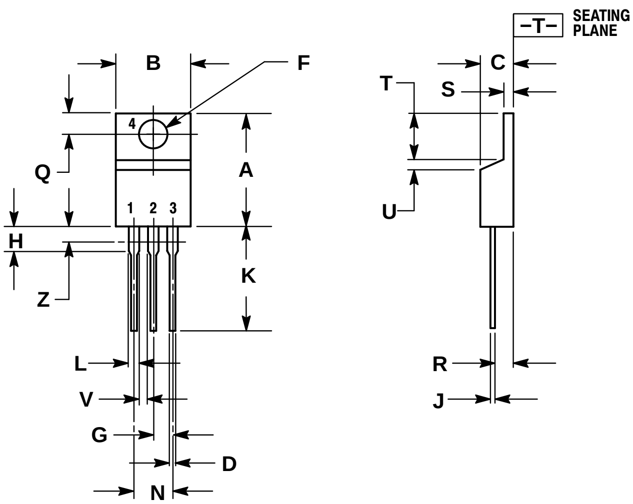
$$W_{AVAL} \approx \frac{1}{2} L I_{LPK}^{2} \left(\frac{BV_{DUT}}{BV_{DUT} - V_{DD}} \right)$$

EQUATION (2):

$$W_{AVAL} \approx \frac{1}{2} L I_{LPK}^{2}$$

PACKAGE DIMENSIONS

TO−220
CASE 221A−09
ISSUE AD



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS	
DIM	**MIN**	**MAX**	**MIN**	**MAX**
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

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